

isc N-Channel MOSFET Transistor

AOT11S65

FEATURES

- Drain Current –I_D=11A@ T_C=25 °C
- Drain Source Voltage-
 - : V_{DSS}=650V(Min)
- Static Drain-Source On-Resistance
 - : $R_{DS(on)} = 0.399 \Omega (Max)$
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

G(1) S(3) pin 1.Gate 2.Drain 3.Source TO-220 package

DESCRIPTION

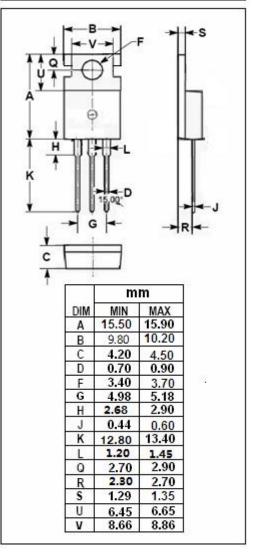
 Designed for use in switch mode power supplies and general purpose applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	650	V
V _{GS}	Gate-Source Voltage-Continuous	±30	V
I _D	Drain Current-Continuous	11	А
I _{DM}	Drain Current-Single Pluse	45	А
P _D	Total Dissipation @T _C =25℃	198	W
TJ	Max. Operating Junction Temperature -55~15		°C
T _{stg}	Storage Temperature -55~150		$^{\circ}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	0.63	°C/W



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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBO L	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 0.25mA	650			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = 5V; I _D = 0.25mA	2.6		4.0	٧
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D = 5.5A			0.399	Ω
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±30V;V _{DS} = 0			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 650V; V _{GS} = 0			1	μА
V _{SD}	Forward On-Voltage	I _S = 5.5A; V _{GS} = 0		0.82		V

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